

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

1. (currently amended) A selective wetting material comprising a photosensitive film on a substrate, the photosensitive film formed from a two-component plasma reaction in a substantially air-evacuated plasma chamber, a first component of the two-component plasma reaction comprising a non-carbon containing and non-oxygenated silicon donor, and a second component of the two-component plasma reaction comprising a non-silicon containing and non-oxygenated organic precursor, the photosensitive film comprising photosensitive (Si-H) and (Si-Si) fragments situated in a non-silicon containing and non-photosensitive organic polymer matrix, the photosensitive film having a one or more selective wetting regions formed from the exposure of the one or more selective wetting regions to a radiated electromagnetic energy in the presence of oxygen, the one or more selective wetting regions comprising silicon oxides formed from oxidation of silicon in the (Si-H) and (Si-Si) fragments, whereby a liquid brought into contact with the photosensitive film selectively wets and adheres to the one or more selective wetting regions of the photosensitive film.
2. (original) The selective wetting material of claim 1 wherein the second component of the two-component plasma reaction is selected from the group consisting of alkanes, alkenes, alkynes, phenyls and aromatic hydrocarbons.
3. (original) The selective wetting material of claim 1 wherein the second component of the two-component plasma reaction is selected from the group consisting of ethylene, methane, ethane and toluene.
4. (original) The selective wetting material of claim 1 wherein the first component of the two-component plasma reaction is selected from the group consisting of monosilane, disilane and dichlorsilane.
5. (original) The selective wetting material of claim 4 wherein the second component of the two-component plasma reaction is selected from the group consisting of ethylene, methane, ethane and toluene.
- 6 - 20. (canceled)
21. (previously presented) The selective wetting material of claim 1 wherein the

radiated electromagnetic energy is ultraviolet light.

22. (currently amended) A selective wetting material comprising a photosensitive film ~~on a substrate~~, the photosensitive film formed from a two-component plasma reaction in a substantially air-evacuated plasma chamber, a first component of the two-component plasma reaction selected from the group consisting of monosilane and disilane, and a second component of the two-component plasma reaction comprising a non-silicon containing and non-oxygenated organic precursor, the photosensitive film comprising photosensitive (Si-H) and (Si-Si) fragments situated in a non-silicon containing and non-photosensitive organic polymer matrix, the photosensitive film having a one or more selective wetting regions formed from the exposure of the one or more selective wetting regions to a radiated electromagnetic energy in the presence of oxygen the one or more selective wetting regions comprising silicon oxides formed from oxidation of silicon in the (Si-H) and (Si-Si) fragments, whereby a liquid brought into contact with the photosensitive film selectively wets and adheres to the one or more selective wetting regions of the film.

23. (previously presented) The selective wetting material of claim 22 wherein the organic precursor is ethylene or toluene.

24. (previously presented) The selective wetting material of claim 23 wherein the ratio of silicon atoms to carbon atoms in the film is approximately 1:7.

25. (previously presented) The selective wetting material of claim 22 wherein the organic precursor is ethylene or toluene and the silicon donor is monosilane with a weight ratio of the organic precursor to the silicon donor of approximately between 1:2 and 1:1.

26. (previously presented) The selective wetting material of claim 22 wherein the organic precursor is selected from the group consisting of alkanes, alkenes, alkynes, phenyls and aromatic hydrocarbons.

27. (previously presented) The selective wetting material of claim 22 wherein the radiated electromagnetic energy is ultraviolet light.

28. (currently amended) A selective wetting material comprising a photosensitive film on a substrate, the photosensitive film formed from a two-component plasma reaction in a substantially air-evacuated plasma chamber, wherein the two components comprise monosilane and an organic precursor selected from the group consisting of ethylene and

toluene, the photosensitive film comprising photosensitive (Si-H) and (Si-Si) fragments situated in a non-silicon containing and non-photosensitive organic polymer matrix, the photosensitive film having a one or more selective wetting regions formed from the exposure of the one or more selective wetting regions to a radiated electromagnetic energy in the presence of oxygen, the one or more selective wetting regions comprising silicon oxides formed from oxidation of silicon in the (Si-H) and (Si-Si) fragments, whereby a liquid brought into contact with the photosensitive film selectively wets and adheres to the one or more selective wetting regions of the photosensitive film.

29. (previously presented) The selective wetting material of claim **28** wherein the weight ratio of the organic precursor to the monosilane is approximately between 1:2 and 1:1 and the ratio of silicon atoms to carbon atoms in the layer of the film is approximately 1:7.

30. (previously presented) The selective wetting material of claim **28** wherein the radiated electromagnetic energy is ultraviolet light.